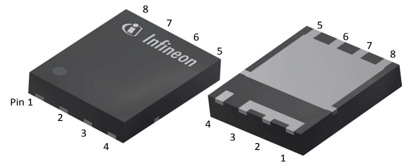
MOSFET

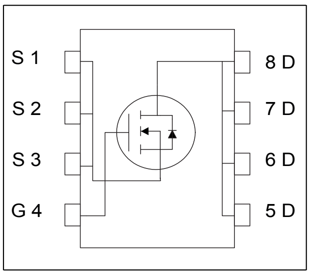
OptiMOS™ Power-Transistor, 100 V

Features

- Optimized for high performance SMPS, e.g. sync. rec.
- 100% avalanche tested
- Superior thermal resistance
- N-channel
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21
- 175°C rated

PG-TSON-8-3





Product validation

Fully qualified according to JEDEC for Industrial Applications

Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	100	V
$R_{DS(on),max}$	2.7	mΩ
I_D	194	A
Q_{oss}	114	nC
Q_G(0V..10V)	89	nC

Type / Ordering Code	Package	Marking	Related Links
BSC027N10NS5	PG-TSON-8-3	027N10N	-

Table of Contents

1 Maximum ratings

at T_A=25 °C, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current[1]	I_D	- - -	- - -	194 137 23	A	V_{GS}=10 V, T_C=25 °C V_{GS}=10 V, T_C=100 °C V_{GS}=10 V, T_A=25 °C, R_{thJA} =50K/W[2]
Pulsed drain current[3]	$I_{D,pulse}$	-	-	776	A	T_C=25 °C
Avalanche energy, single pulse[4]	E_{AS}	-	-	641	mJ	I_D=50 A, R_{GS}=25 Ω
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	- -	- -	214 3.0	W	T_C=25 °C T_A=25 °C, R_{thJA}=50 K/W[3]
Operating and storage temperature	T_j, T_{stg}	-55	-	175	°C	IEC climatic category; DIN IEC 68-1: 55/175/56

2 Thermal characteristics

at T_j=25 °C, unless otherwise specified

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case, bottom	R_{thJC}	-	0.4	0.7	K/W	-
Thermal resistance, junction - case, top	R_{thJC}	-	-	20	K/W	-
Device on PCB, 6 cm² cooling area[2]	R_{thJA}	-	-	50	K/W	-

[1] Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature as specified. For other case temperatures please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.
[2] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm2 (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.
[3] See Diagram 3 for more detailed information
[4] See Diagram 13 for more detailed information

3 Electrical characteristics

at T_j=25 °C, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	100	-	-	V	V_{GS}=0 V, I_D=1 mA
Gate threshold voltage	$V_{GS(th)}$	2.2	3.0	3.8	V	V_{DS}=V_{GS}, I_D=146 µA
Zero gate voltage drain current	I_{DSS}	- -	0.1 10	5 100	µA	V_{DS}=100 V, V_{GS}=0 V, T_j=25 °C V_{DS}=100 V, V_{GS}=0 V, T_j=125 °C
Gate-source leakage current	I_{GSS}	-	10	100	nA	V_{GS}=20 V, V_{DS}=0 V
Drain-source on-state resistance	$R_{DS(on)}$	- -	2.1 2.6	2.7 3.4	mΩ	V_{GS}=10 V, I_D=50 A V_{GS}=6 V, I_D=25 A
Gate resistance[1]	R_G	-	1.7	2.5	Ω	-
Transconductance	g_{fs}	75	150	-	S	$\|V_{DS}\|>2\|I_D\|R_{DS(on)max}$, I_D=50 A

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance[1]	C_{iss}	-	6300	8200	pF	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz
Output capacitance[1]	C_{oss}	-	970	1300	pF	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz
Reverse transfer capacitance[1]	C_{rss}	-	43	75	pF	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz
Turn-on delay time	$t_{d(on)}$	-	13	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=50 A, $R_{G,ext}$=3 Ω
Rise time	t_r	-	14	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=50 A, $R_{G,ext}$=3 Ω
Turn-off delay time	$t_{d(off)}$	-	41	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=50 A, $R_{G,ext}$=3 Ω
Fall time	t_f	-	18	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=50 A, $R_{G,ext}$=3 Ω

Table 6 Gate charge characteristics[2]

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	28	-	nC	V_{DD}=50 V, I_D=50 A, V_{GS}=0 to 10 V
Gate charge at threshold	$Q_{g(th)}$	-	19	-	nC	V_{DD}=50 V, I_D=50 A, V_{GS}=0 to 10 V
Gate to drain charge[1]	Q_{gd}	-	18	27	nC	V_{DD}=50 V, I_D=50 A, V_{GS}=0 to 10 V
Switching charge	Q_{sw}	-	27	-	nC	V_{DD}=50 V, I_D=50 A, V_{GS}=0 to 10 V
Gate charge total[1]	Q_g	-	89	111	nC	V_{DD}=50 V, I_D=50 A, V_{GS}=0 to 10 V
Gate plateau voltage	$V_{plateau}$	-	4.4	-	V	V_{DD}=50 V, I_D=50 A, V_{GS}=0 to 10 V
Gate charge total, sync. FET	$Q_{g(sync)}$	-	77	-	nC	V_{DS}=0.1 V, V_{GS}=0 to 10 V
Output charge[1]	Q_{oss}	-	114	152	nC	V_{DD}=50 V, V_{GS}=0 V

[1] Defined by design. Not subject to production test
[2] See "Gate charge waveforms" for parameter definition

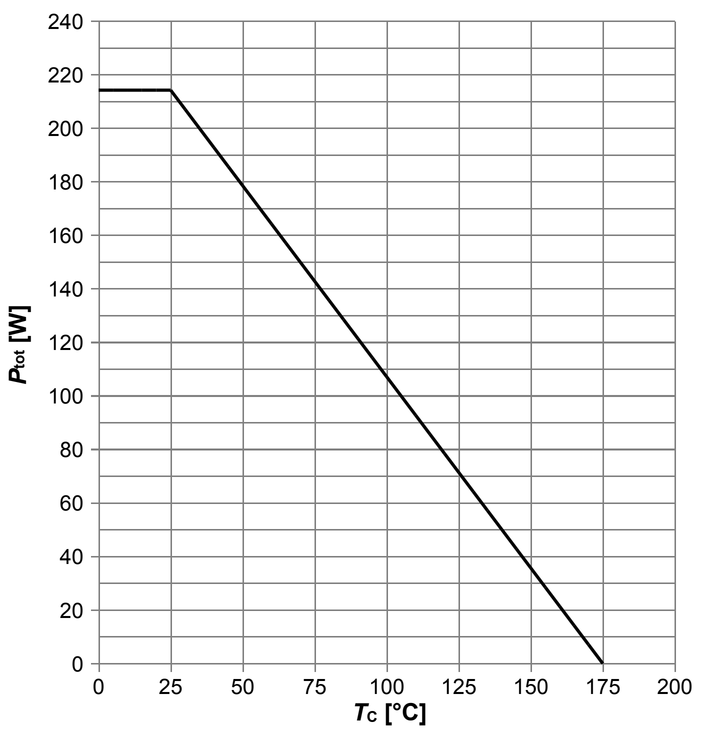
Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	162	A	T_C=25 °C
Diode pulse current	$I_{S,pulse}$	-	-	776	A	T_C=25 °C
Diode forward voltage	V_{SD}	-	0.83	1.1	V	V_{GS}=0 V, I_F=50 A, T_j=25 °C
Reverse recovery time[1)	t_{rr}	-	56	112	ns	V_R=50 V, I_F=50 A, di_F/dt=100 A/µs
Reverse recovery charge[1)	Q_{rr}	-	89	178	nC	V_R=50 V, I_F=50 A, di_F/dt=100 A/µs

[1)] Defined by design. Not subject to production test

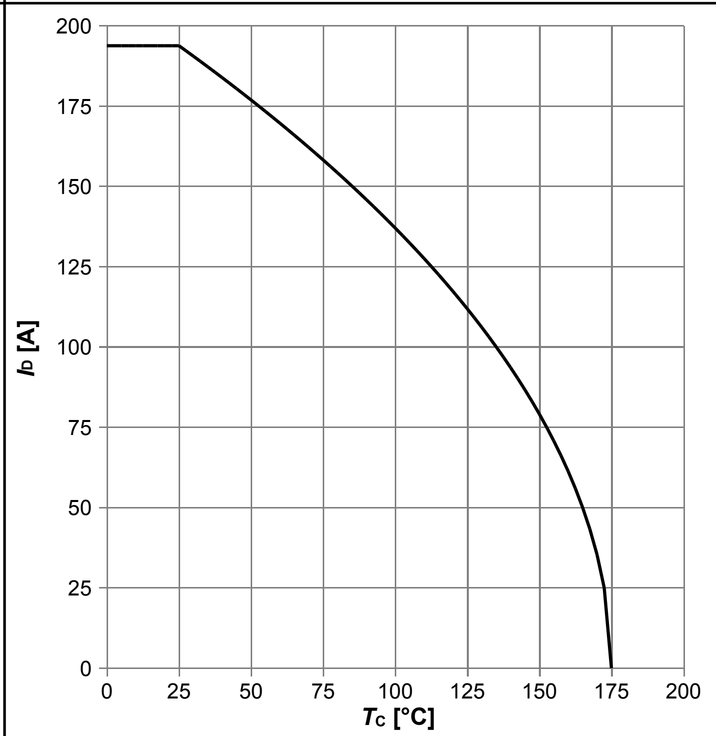
4 Electrical characteristics diagrams

Diagram 1: Power dissipation



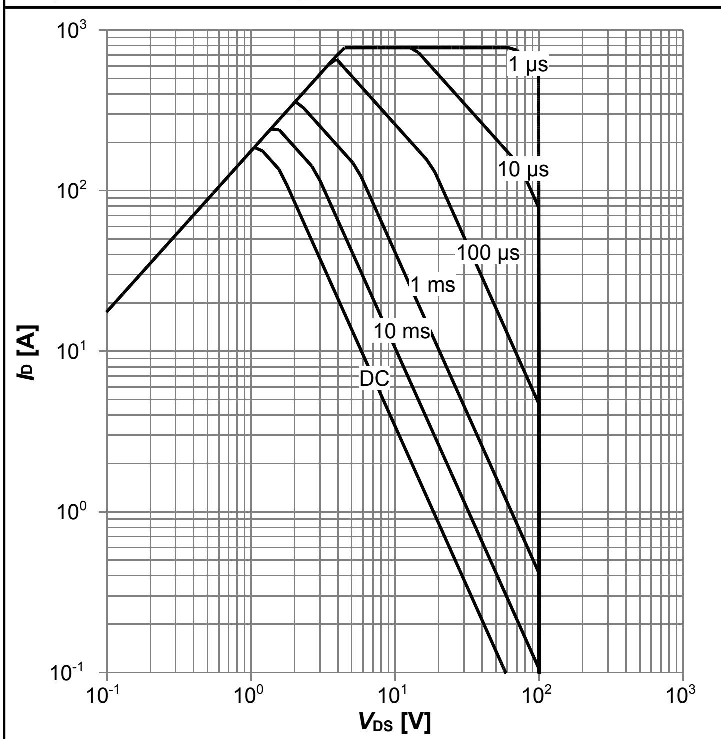
P_{tot}=f(T_C)

Diagram 2: Drain current



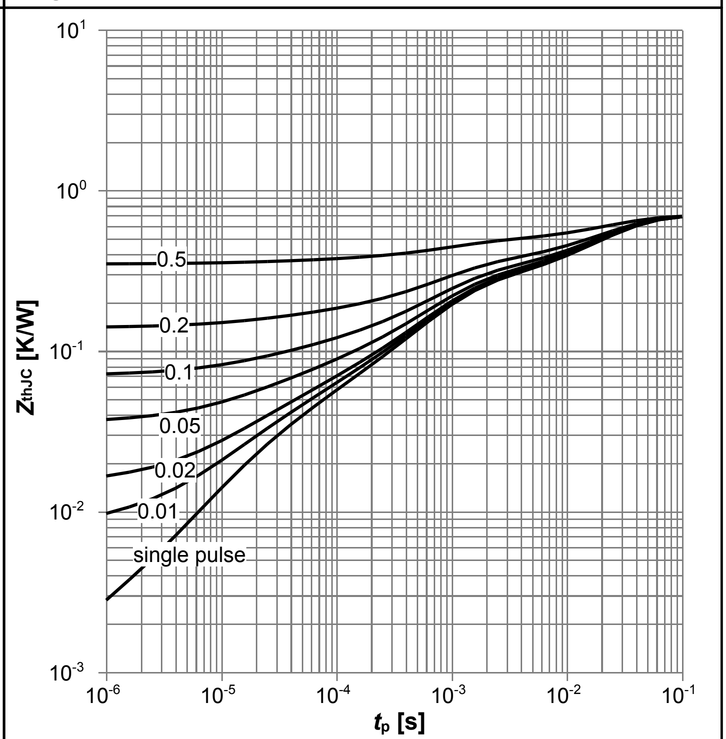
I_D=f(T_C); V_{GS}≥10 V

Diagram 3: Safe operating area



I_D=f(V_{DS}); T_C=25 °C; D=0; parameter: t_p

Diagram 4: Max. transient thermal impedance



Z_{thJC}=f(t_p); parameter: D=t_p/T

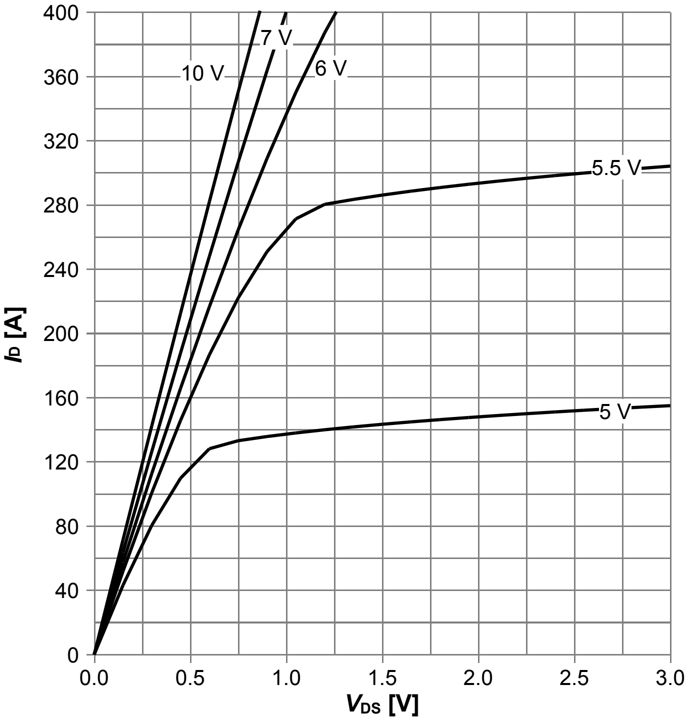
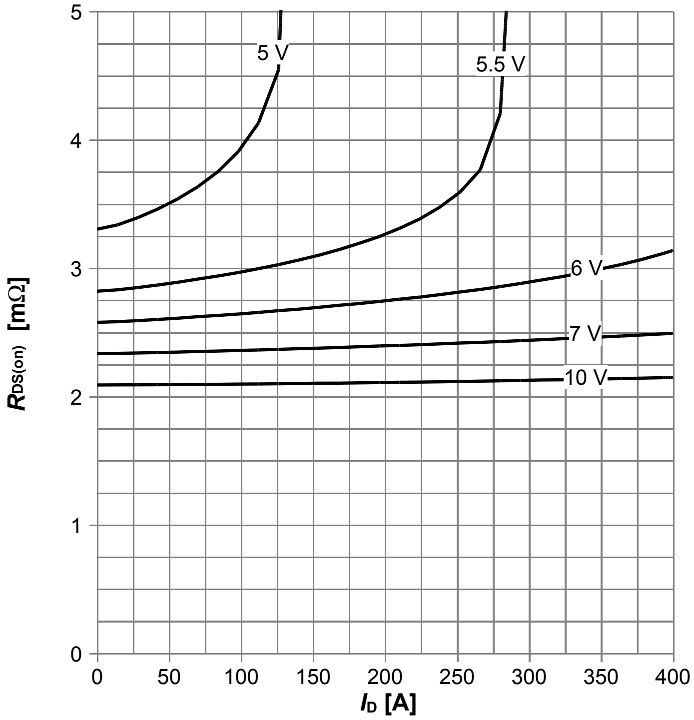
Diagram 5: Typ. output characteristics	**Diagram 6: Typ. drain-source on resistance**
	
I_D=f(V_{DS}); T_j=25 °C; parameter: V_{GS}	$R_{DS(on)}$=f(I_D); T_j=25 °C; parameter: V_{GS}

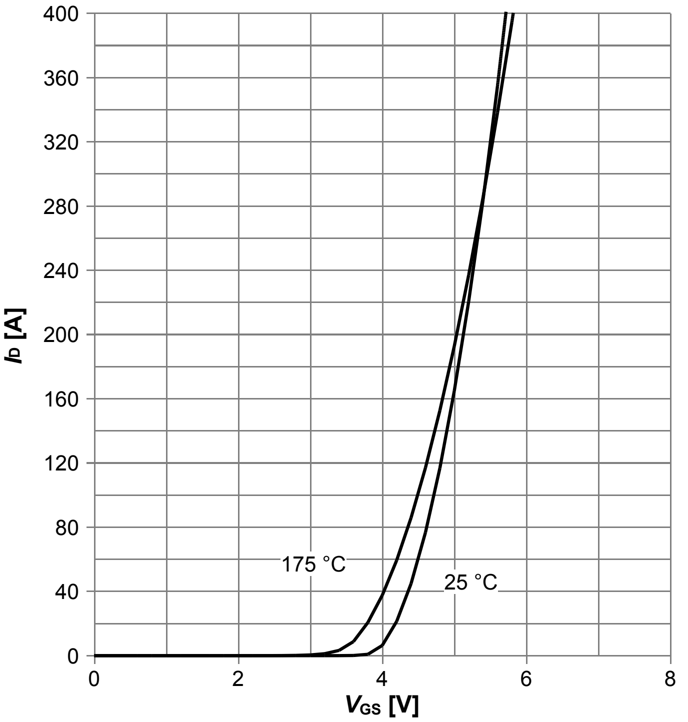
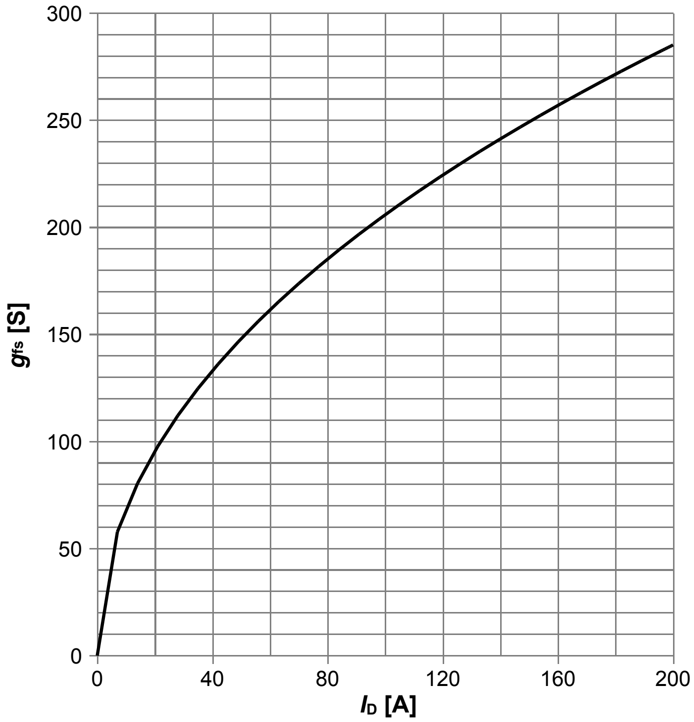
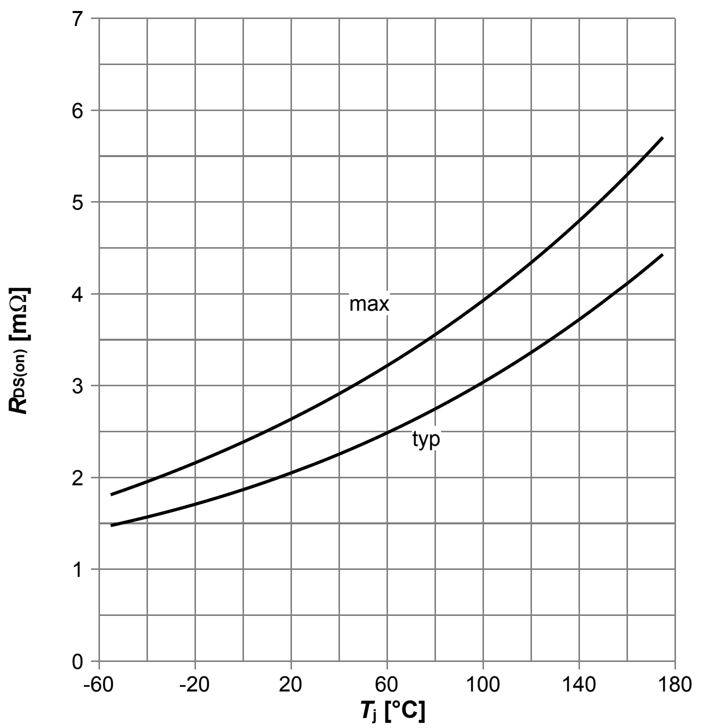
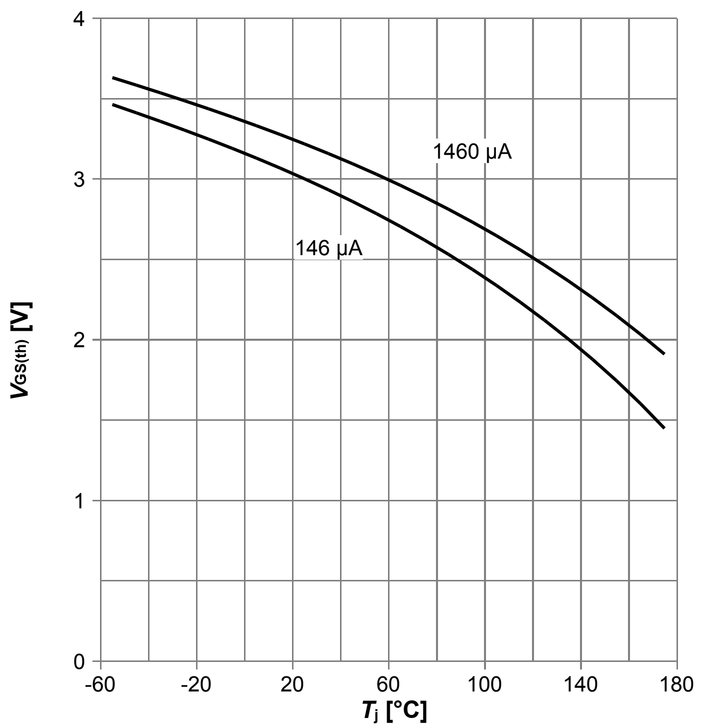
Diagram 7: Typ. transfer characteristics	**Diagram 8: Typ. forward transconductance**
	
I_D=f(V_{GS}); |V_{DS}|>2|I_D|$R_{DS(on)max}$; parameter: T_j	g_{fs}=f(I_D); T_j=25 °C

Diagram 9: Drain-source on-state resistance



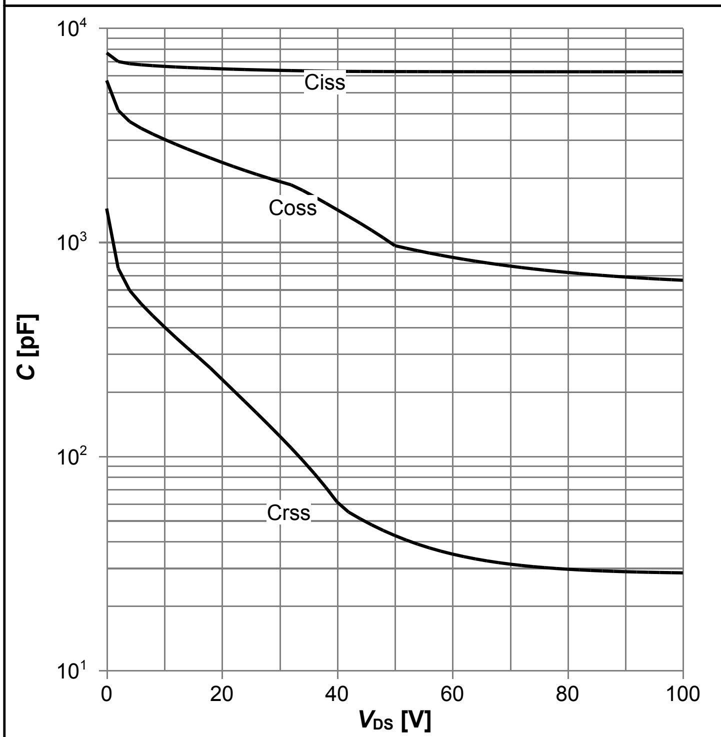
$R_{DS(on)}=f(T_j)$; I_D=50 A; V_{GS}=10 V

Diagram 10: Typ. gate threshold voltage



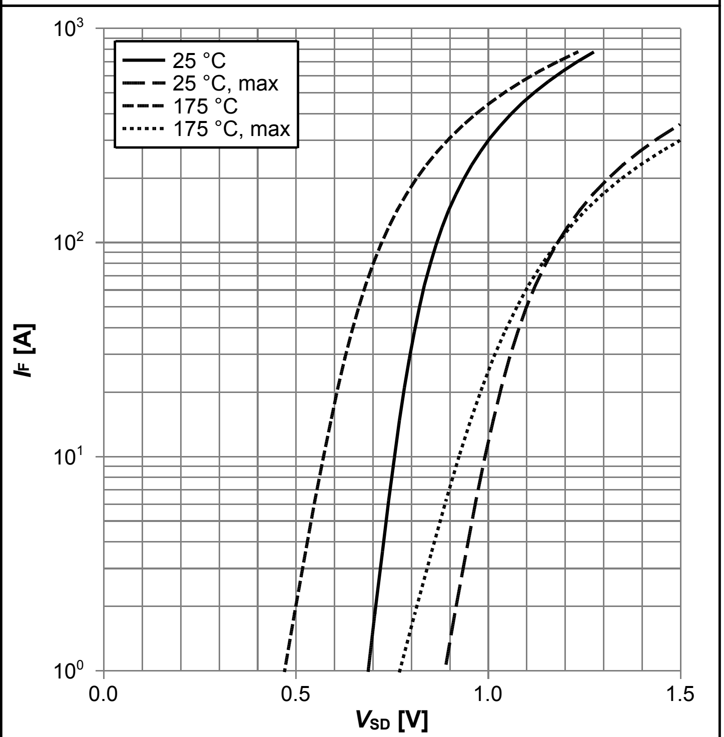
$V_{GS(th)}=f(T_j)$; $V_{GS}=V_{DS}$

Diagram 11: Typ. capacitances



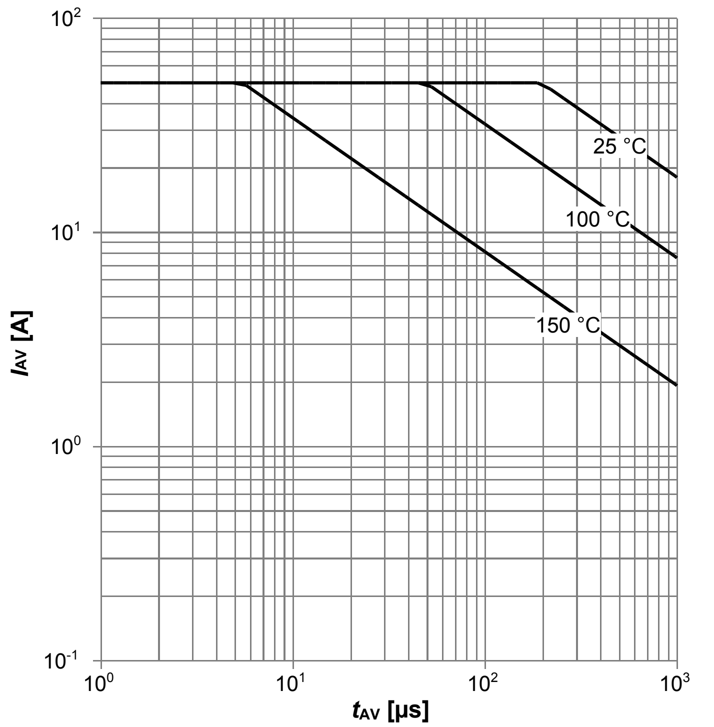
$C=f(V_{DS})$; V_{GS}=0 V; f=1 MHz

Diagram 12: Forward characteristics of reverse diode



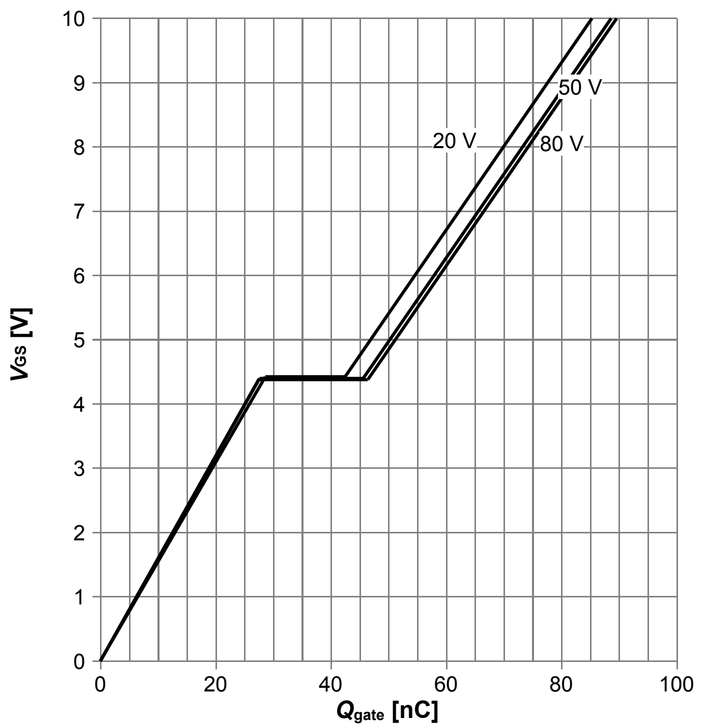
$I_F=f(V_{SD})$; parameter: T_j

Diagram 13: Avalanche characteristics



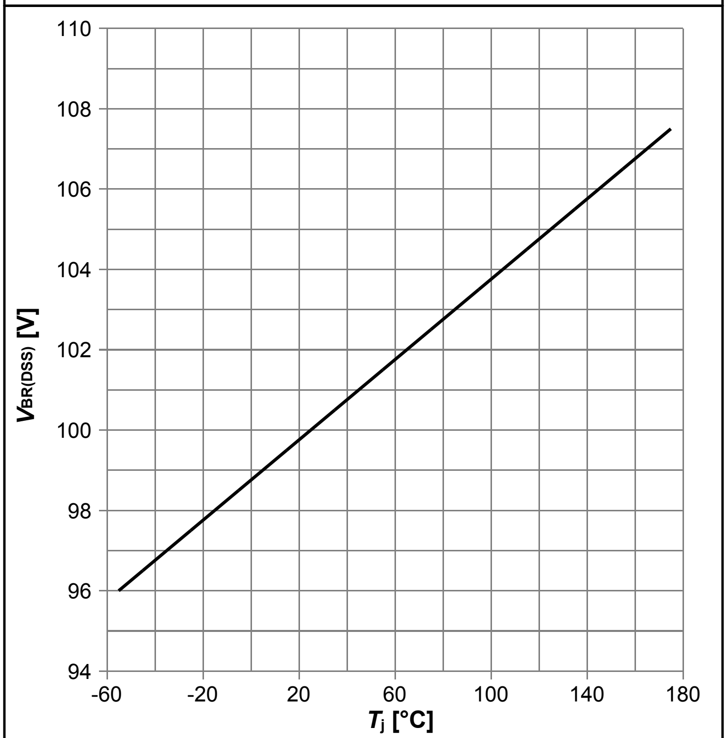
I_{AS}=f(t_{AV}); R_{GS}=25 Ω; parameter: $T_{j(start)}$

Diagram 14: Typ. gate charge



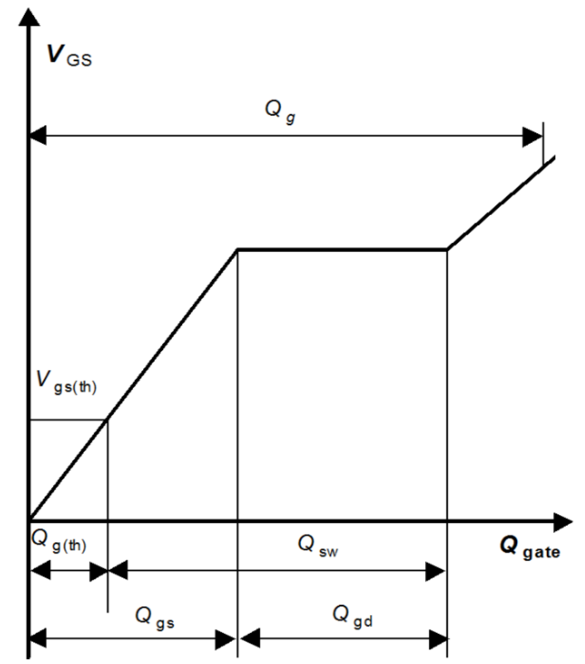
V_{GS}=f(Q_{gate}); I_D=50 A pulsed; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage

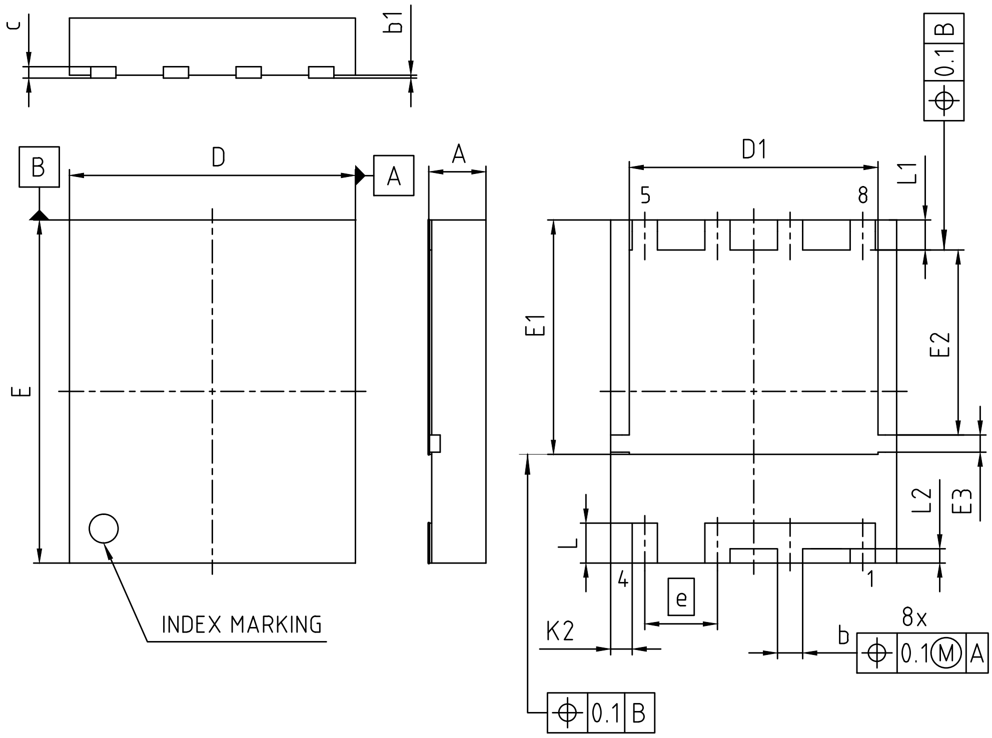


$V_{BR(DSS)}$=f(T_j); I_D=1 mA

Diagram Gate charge waveforms



5 Package Outlines



DIMENSION	MILLIMETERS	
	MIN.	MAX.
A	-	1.10
b	0.34	0.54
b1	-	0.05
c	0.20	
D	4.90	5.10
D1	4.25	4.45
E	5.90	6.10
E1	4.00	4.20
E2	3.14	3.34
E3	0.20	0.40
e	1.27	
K2	(0.37)	
L	0.60	0.80
L1	0.43	0.63
L2	(0.25)	

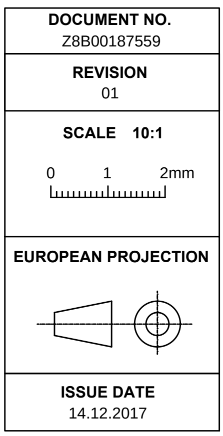


Figure 1 Outline PG-TSON-8-3, dimensions in mm/inches

Revision History

BSC027N10NS5

Revision: 2020-11-26, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2018-02-28	Release of final version
2.1	2020-11-26	Update current rating

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